Enxiu Wu

List of Publications by Year
in descending order

24 papers	697 citations	687363 13 h-index	610901 24 g-index
24 all docs	24 docs citations	24 times ranked	1136 citing authors

#	Article	IF	Citations
1	Ultrasensitive and Fully Reversible NO_2 Gas Sensing Based on p-Type $MoTe_2$ under Ultraviolet Illumination. ACS Sensors, 2018, 3, 1719-1726.	7.8	135
2	Dynamically controllable polarity modulation of $MoTe_2$ field-effect transistors through ultraviolet light and electrostatic activation. Science Advances, 2019, 5, eaav3430.	10.3	96
3	Photoinduced Doping To Enable Tunable and High-Performance Anti-Ambipolar $MoTe_2$/MoS_2 Heterotransistors. ACS Nano, 2019, 13, 5430-5438.	14.6	73
4	Contact Engineering of Molybdenum Ditelluride Field Effect Transistors through Rapid Thermal Annealing. ACS Applied Materials & Interfaces, 2017, 9, 30107-30114.	8.0	37
5	Multifunctional anti-ambipolar p-n junction based on MoTe2/MoS2 heterostructure. Applied Physics Letters, 2019, 115, .	3.3	35
6	Specific and Highly Sensitive Detection of Ketone Compounds Based on p-Type $MoTe_2$ under Ultraviolet Illumination. ACS Applied Materials & Interfaces, 2018, 10, 35664-35669.	8.0	34
7	Gate-Tunable Photodetection/Voltaic Device Based on BP/$MoTe_2$ Heterostructure. ACS Applied Materials & Interfaces, 2019, 11, 14215-14221.	8.0	34
8	Highly-sensitive gas sensor based on two-dimensional material field effect transistor. Nanotechnology, 2018, 29, 435502.	2.6	32
9	Acoustically enhanced photodetection by a black phosphorusâ€"MoS_2 van der Waals heterojunction pâ€"n diode. Nanoscale, 2018, 10, 10148-10153.	5.6	31
10	Enhanced Sensitivity of MoTe2 Chemical Sensor through Light Illumination. Micromachines, 2017, 8, 155.	2.9	30
11	Enhancing electronic and optoelectronic performances of tungsten diselenide by plasma treatment. Nanoscale, 2018, 10, 12436-12444.	5.6	30
12	Multi-level flash memory device based on stacked anisotropic ReS_2â€"boron nitrideâ€"graphene heterostructures. Nanoscale, 2020, 12, 18800-18806.	5.6	27
13	Frequency doubler based on a single MoTe2/MoS2 anti-ambipolar heterostructure. Applied Physics Letters, 2020, 117, .	3.3	20
14	Non-volatile programmable homogeneous lateral MoTe2 junction for multi-bit flash memory and high-performance optoelectronics. Nano Research, 2020, 13, 3445-3451.	10.4	11
15	Tunable and nonvolatile multibit data storage memory based on $MoTe_2$/boron nitride/graphene heterostructures through contact engineering. Nanotechnology, 2020, 31, 485205.	2.6	11
16	Side-liquid-gated electrochemical transistors and their neuromorphic applications. Journal of Materials Chemistry C, 2021, 9, 16655-16663.	5.5	11
17	Gate-tunable van der Waals heterostructure based on semimetallic WTe2 and semiconducting MoTe2. Applied Physics Letters, 2021, 118, .	3.3	10
18	Anomalous Acoustoelectric Currents in Few-Layer Black Phosphorus Nanocrystals. IEEE Nanotechnology Magazine, 2018, 17, 590-595.	2.0	8

#	Article	IF	Citations
19	Dielectric engineering enable to lateral anti-ambipolar $MoTe_2$ heterojunction. Nanotechnology, 2022, 33, 175704.	2.6	8
20	Flash memory based on MoTe2/boron nitride/graphene semi-floating gate heterostructure with non-volatile and dynamically tunable polarity. Nano Research, 2022, 15, 6507-6514.	10.4	6
21	The effect of air stable n-doping through mild plasma on the mechanical property of WSe_2 layers. Nanotechnology, 2018, 29, 175703.	2.6	5
22	Volatile organic compounds discrimination based on dual mode detection. Nanotechnology, 2018, 29, 245502.	2.6	5
23	Modulation of $MoTe_2$/MoS_2 van der Waals heterojunctions for multifunctional devices using N_2O plasma with an opposite doping effect. Nanoscale, 2021, 13, 7851-7860.	5.6	5
24	UV light modulated synaptic behavior of $MoTe_2$/BN heterostructure. Nanotechnology, 2021, 32, 475207.	2.6	3